



PCN# : P692AAB
Issue Date : Jan. 03, 2017

DESIGN/PROCESS CHANGE NOTIFICATION

This is to inform you that a change is being made to the products listed below.

Unless otherwise indicated in the details of this notification, the identified change will have no impact on product quality, reliability, electrical, visual or mechanical performance and affected products will remain fully compliant to all published specifications. Products incorporating this change may be shipped interchangeably with existing unchanged products.

This change is planned to take effect in 90 calendar days from the date of this notification. Please work with your local ON Sales Representative to manage your inventory of unchanged product if your evaluation of this change will require more than 90 calendar days.

Please contact your local Customer Quality Engineer within 30 days of receipt of this notification if you require any additional data or samples.

Implementation of change:

Expected First Shipment Date for Changed Product :Apr. 03, 2017

Expected First Date Code of Changed Product :1715

Description of Change (From) :
Wafer fabrication of PT1 products at TowerJazz Israel

Description of Change (To) :
8-inch wafer fabrication of PT1 products at ON Semiconductor Bucheon, South Korea and TowerJazz Israel

Reason for Change:
ON Semiconductor is increasing wafer fabrication capacity by qualifying 8-inch wafer fabrication line at ON Semiconductor Bucheon Korea.
Quality and reliability remain at the highest standards already demonstrated within ON Semiconductor's existing products.
The reliability qualification results used to qualify the 8-inch wafer fabrication line are summarized below.
Design, die size and layout of the affected products will remain unchanged. There are no changes in the datasheet or electrical performance.



Affected Product(s):

BSS84_G	FDB8030L	FDC2512
FDC3512	FDC3535	FDC5614P
FDC642P_G	FDC658P_NB4E011	FDD2670
FDD3510H	FDD3670	FDD3680
FDD3690	FDD5612	FDD5614P
FDD5670	FDD5680	FDD5690
FDD6530A	FDD6630A	FDD6630A_B5N004A
FDFS2P106A	FDMC5614P	FDN336P
FDN342P	FDN5630	FDN5630_G
FDP6030BL	FDS3512	FDS3580
FDS4435A	FDS4488	FDS5690
FDS5690_NBBM009A	FDS6570A	FDS6612A_NB5E029A
FDS6675	FDS6680A_NBBI005A	FDS6690A_NBBM015A
FDS6961A	FDS8935	FDT3612_SN00151
NDT2955	SI3443DV	SI4532DY
SI4542DY		

Qualification Plan	Device	Package	Process	No. of Lots
Q20150480	FDS4559_F085	SOIC-8 Dual	PT1 N/P	2 (1*)

Test Description:	Condition:	Standard :	Duration:	Results:
MSL1 Preconditioning	260C, 3x reflow	JESD22-A113	NA	0/924
Highly Accelerated Stress Test	MSL 1 Preconditioning 130C, 85%RH, Vr=+/-42V	JESD22-A110	96 hrs	0/231
Un-biased Highly Accelerated Stress Test	MSL 1 Preconditioning 130C, 85%RH	JESD22-A110	96 hrs	0/231
High Temperature Gate Bias	150C, Vgs=100% of rated Vgs	JESD22-A108	1000hrs	0/231
High Temperature Reverse Bias	150C, Vr=100% of rate BV	JESD22-A108	1000hrs	0/231
Power Cycle	MSL 1 Preconditioning Delta Tj=100C, 2min on/off	JESD22-A105	15000 cycles	0/231
Temperature Cycle	MSL 1 Preconditioning -55C, 150C	JESD22-A104	1000 cycles	0/231

2 (1*): 2 lots for N channel die and 1 lot for P channel die

Qualification Plan	Device	Package	Process	No. of Lots
Q20150479	FDB8030L	TO263	PT1 N	1

Test Description:	Condition:	Standard :	Duration:	Results:
MSL1 Preconditioning	245C, 3x reflow	JESD22-A113	NA	0/385
Highly Accelerated Stress Test	MSL 1 Preconditioning 130C, 85%RH, Vr=24V	JESD22-A110	96 hrs	0/77
Un-biased Highly Accelerated Stress Test	MSL 1 Preconditioning 130C, 85%RH	JESD22-A110	96 hrs	0/77
High Temperature Gate Bias	175C, Vgs=100% of rated Vgs	JESD22-A108	1000 hrs	0/77
High Temperature Reverse Bias	175C, Vr=80% of rated BV	JESD22-A108	1000hrs	0/77
Power Cycle	MSL 1 Preconditioning Delta Tj=100C, 3.5min on/off	JESD22-A105	8572 cycles	0/77
Temperature Cycle	MSL 1 Preconditioning -55C, 150C	JESD22-A104	1000 cycles	0/77
High Temperature Storage Life	MSL 1 Preconditioning 150C	JESD22-A103	1000 cycles	0/77
Resistance to Solder Heat	260C	JESD22-B016	10 sec	0/10

Qualification Plan	Device	Package	Process	No. of Lots
Q20150479	FDC2612	SSOT6	PT1 N	1

Test Description:	Condition:	Standard :	Duration:	Results:
MSL1 Preconditioning	260C, 3x reflow	JESD22-A113	NA	0/385
Highly Accelerated Stress Test	MSL 1 Preconditioning 130C, 85%RH, Vr=80% of rated BV	JESD22-A110	96 hrs	0/77
Un-biased Highly Accelerated Stress Test	MSL 1 Preconditioning 130C, 85%RH	JESD22-A110	96 hrs	0/77
High Temperature Gate Bias	150C, Vgs=100% of rated Vgs	JESD22-A108	1000 hrs	0/77
High Temperature Reverse Bias	150C, Vr=80% of rated BV	JESD22-A108	1000hrs	0/77
High Temperature Storage Life	MSL 1 Preconditioning 150C	JESD22-A103	1000 cycles	0/77
Power Cycle	MSL 1 Preconditioning Delta Tj=100C, 2min on/off	JESD22-A105	10000 cycles	0/77
Temperature Cycle	MSL 1 Preconditioning -55C, 150C	JESD22-A104	1000 cycles	0/77
Resistance to Solder Heat	260C	JESD22-B016	10 sec	0/30

Qualification Plan	Device	Package	Process	No. of Lots
Q20150479 Q20160604	FDC6306P	SSOT6	PT1 P	1

Test Description:	Condition:	Standard :	Duration:	Results:
MSL1 Preconditioning	260C, 3 cycles	JESD22-A113	NA	0/385
Un-biased Highly Accelerated Stress Test	MSL 1 Preconditioning 130C, 85%RH	JESD22-A110	96 hrs	0/77
Highly Accelerated Stress Test	MSL 1 Preconditioning 130C, 85%RH, Vr=80% of rated BV	JESD22-A110	96 hrs	0/77
High Temperature Gate Bias	150C, Vgs=100% of rated Vgs	JESD22-A108	1000 hrs	0/77
High Temperature Reverse Bias	150C, Vr=80% of rated BV	JESD22-A108	1000hrs	0/77
Power Cycle	MSL 1 Preconditioning Delta Tj=100C, 2min on/off	JESD22-A105	10000 cycles	0/77
Temperature Cycle	MSL 1 Preconditioning -55C, 150C	JESD22-A104	1000 cycles	0/77
Resistance to Solder Heat	260C	JESD22-B016	10 sec	0/30
High Temperature Storage Life	MSL 1 Preconditioning 150C	JESD22-A103	1000 cycles	0/77